



# E for Extension

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# Engineering Development

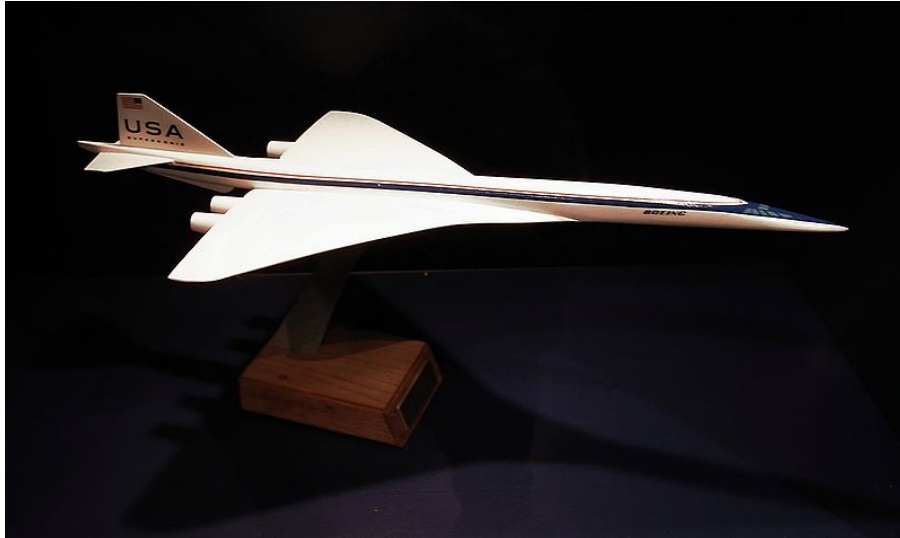


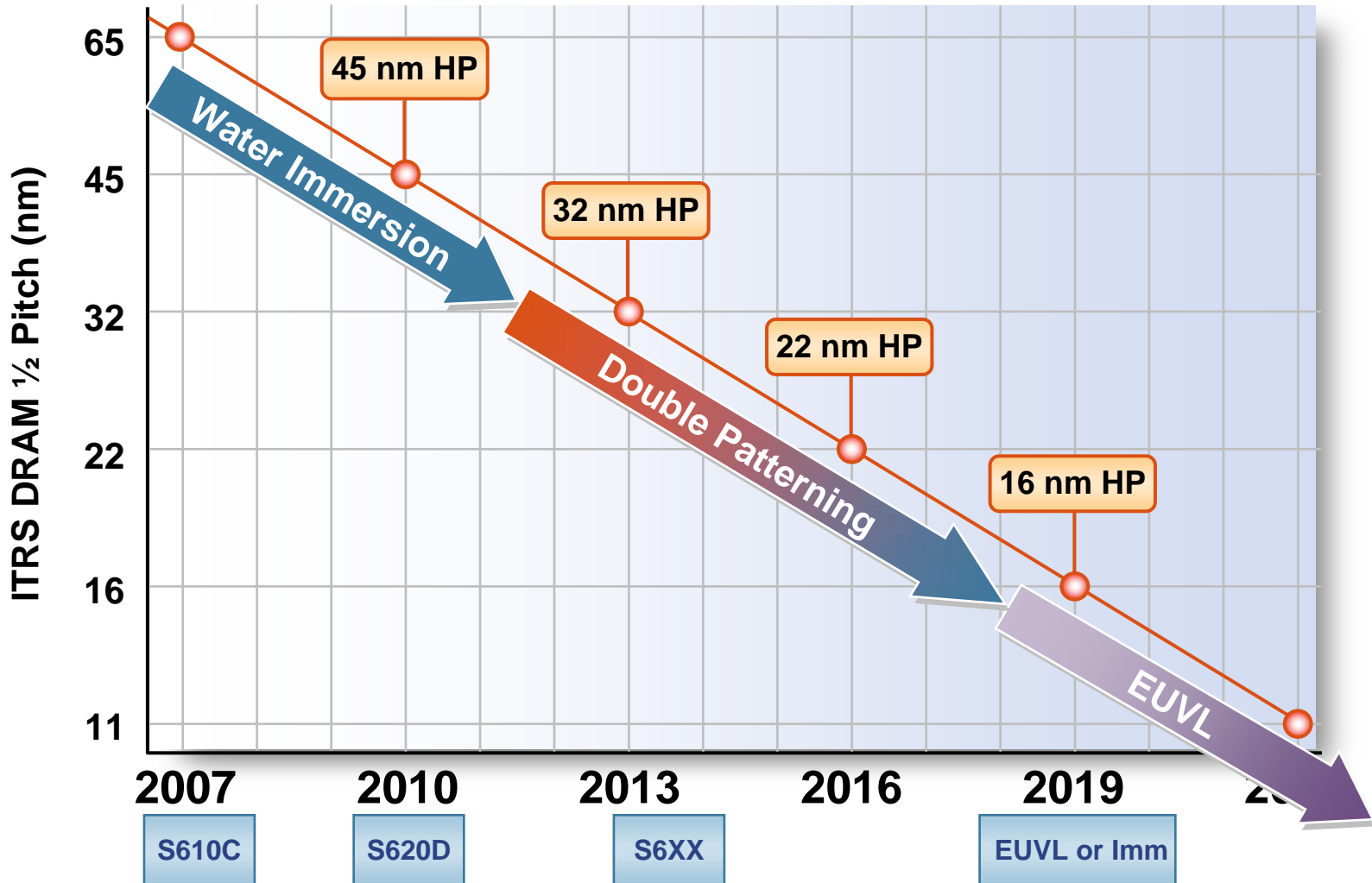
Photo: J. Mabel



Photo: A. Pingstone

- Both of these were designed at the same time
- One appeared to be clearly superior
- One was more successful

# Lithography Roadmap



**ArFi extension takes us to 22 nm at least**

# EUVL and Optical Extensions



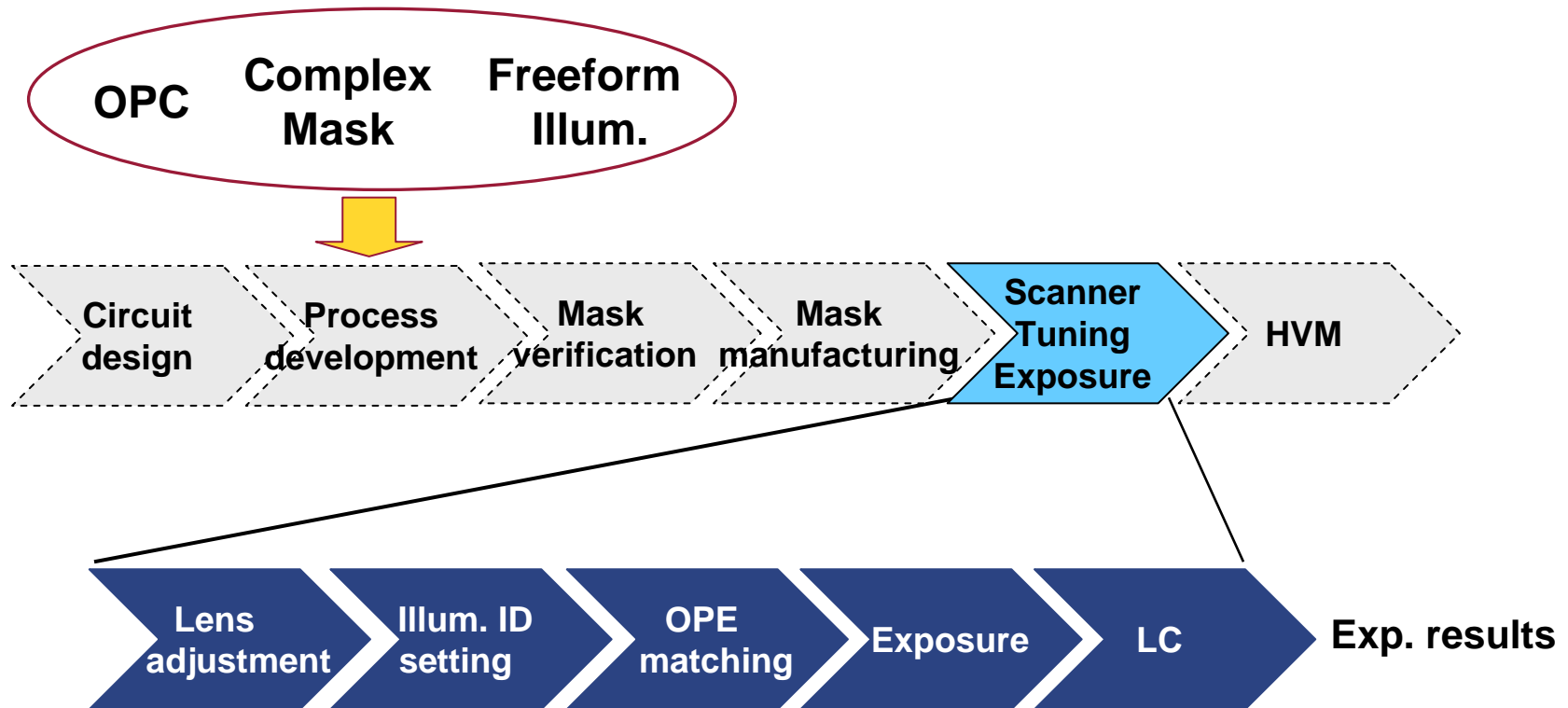
Photo: A. Pingstone

Successful  
technologies get  
extended

1. EUVL clearly offers unbeatable resolution, but its adoption has been delayed due to challenges in parts of the infrastructure or “ecosystem” including light sources and resist.
2. Nikon will support ArF extension to ~20 nm hp while continuing development of EUVL for possible use at 16 nm and beyond.

# Today's Low $k_1$ System

- Aircraft were extended by complicated aerodynamic calculations
- Similarly, ArFi is extended by computational lithography

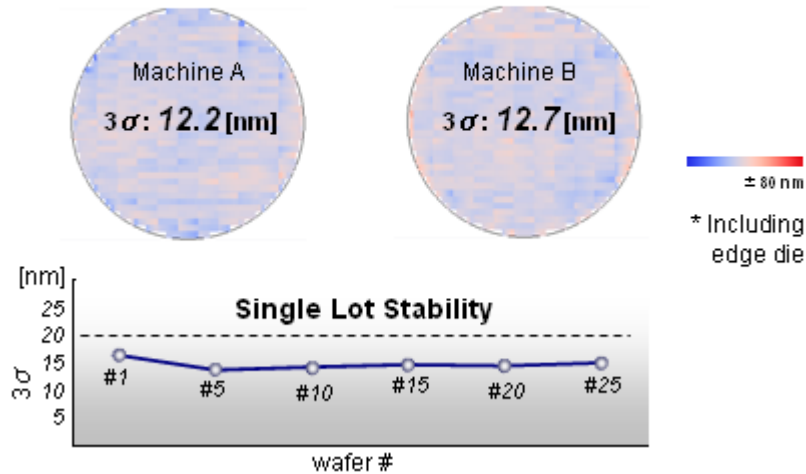


**Systematic & automatic tool setting techniques are needed**

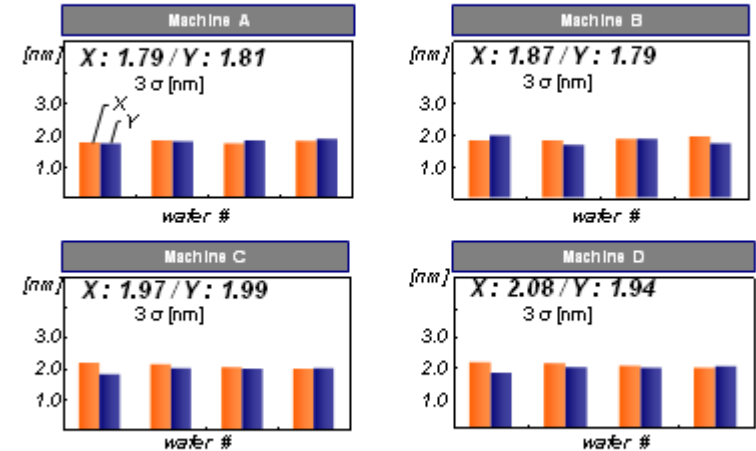
# State-of-the-Art Tooling – S620D



## Focus Uniformity and Stability

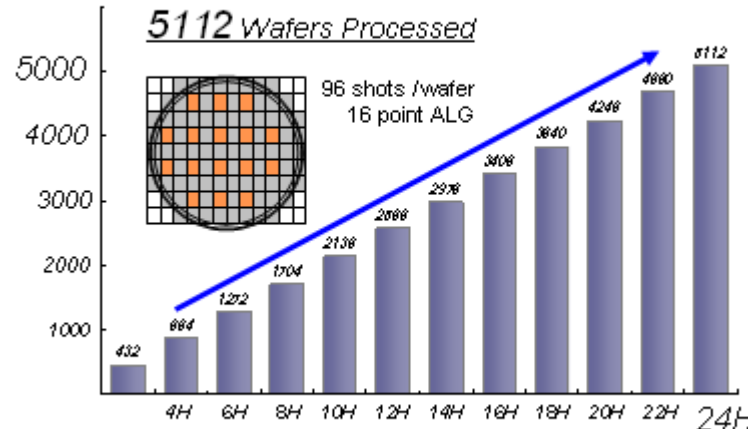


## Single Machine Overlay



Overlay 2 nm at 700 mm/s

## 5000 wpd In-house Running



5000 wpd has been Demonstrated

# System Needs for ArFi Extension



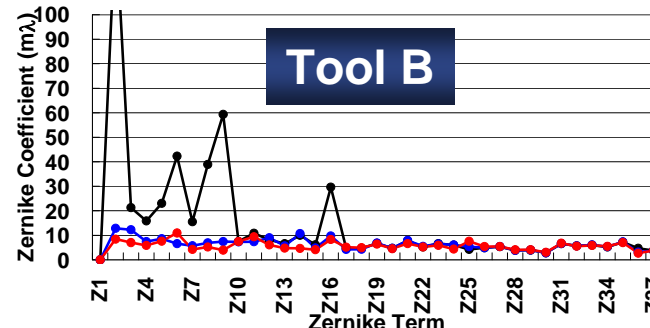
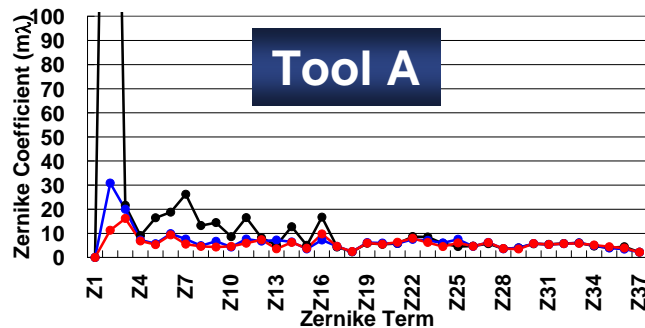
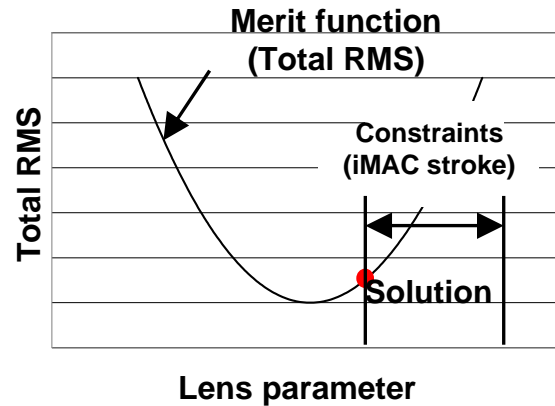
- **Body:**
  - Very precise overlay to support Double Patterning
  - Reduction of focus variation
- **Optics:**
  - Automatic lens setup
  - Custom illumination and software to support OPE signature matching
  - Programmable illumination for OPC/OPE control and for SMO
  - Tight control of thermally-induced lens aberrations
- **General:**
  - Reduction of CDU variation via scanner corrections
  - Support of other lithographic methods

# Lens Aberration Optimizer for Auto-Setup



- Global lens aberration optimization available
- Lens aberration customization (NA, Field, Pattern dependent)

Mathematical method



**LAO automatically optimizes the lens just like a skilled human expert**

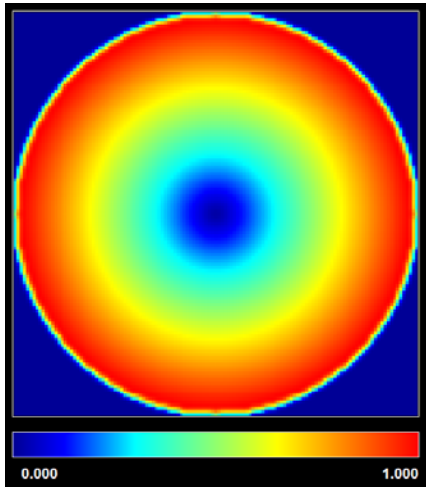
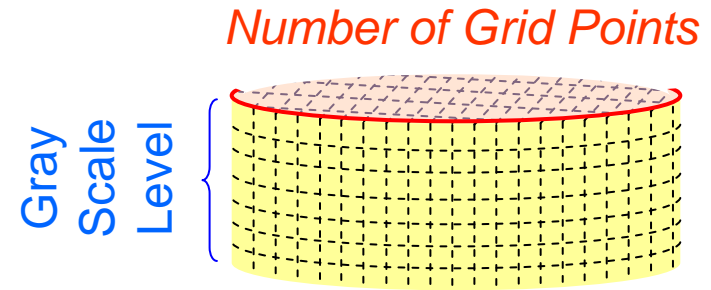


# Pupilgram Control: Intelligent Illuminator

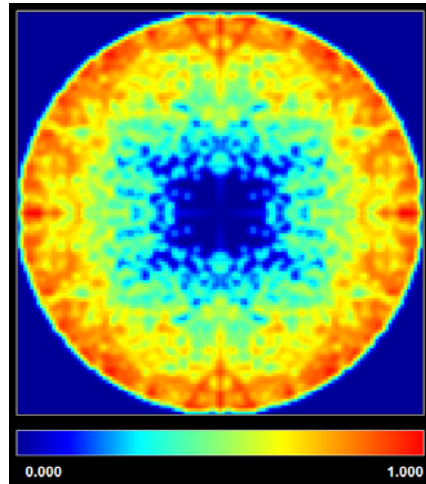


- Pupil fidelity vs. DPF

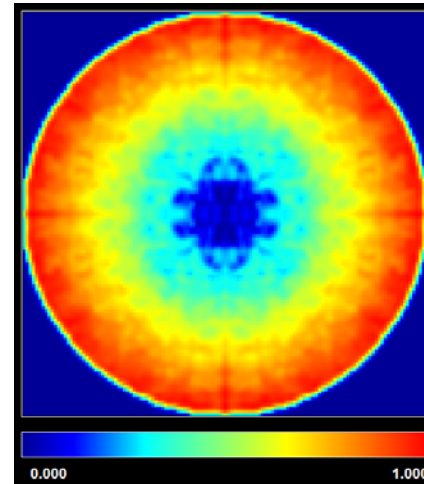
- degree of pupilgram freedom:  
Gray scale level  $\times$  number of grid points



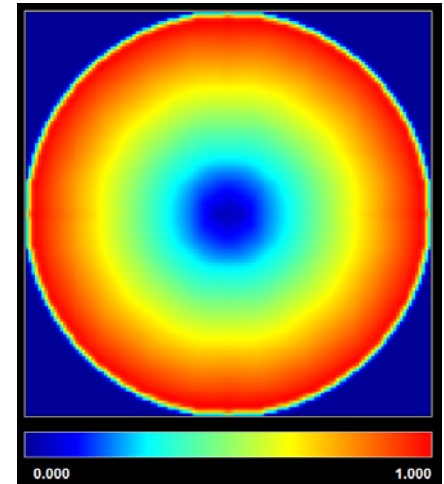
Target



DPF = 4000



DPF = 10,000

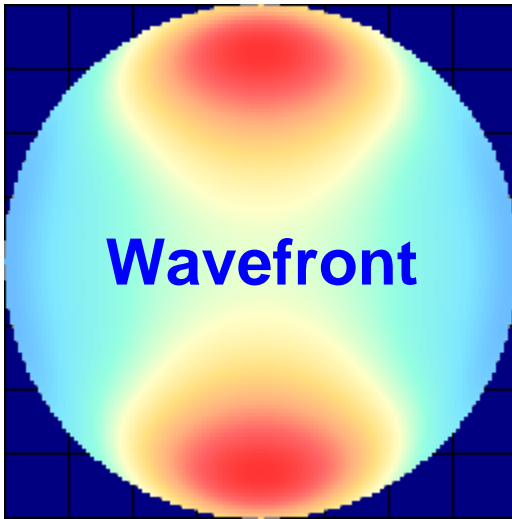


DPF = 100,000

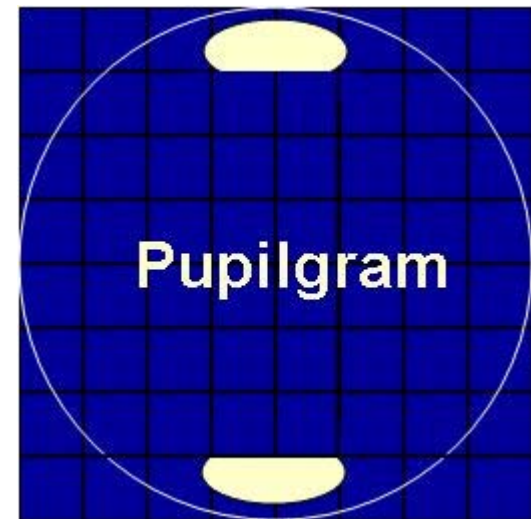
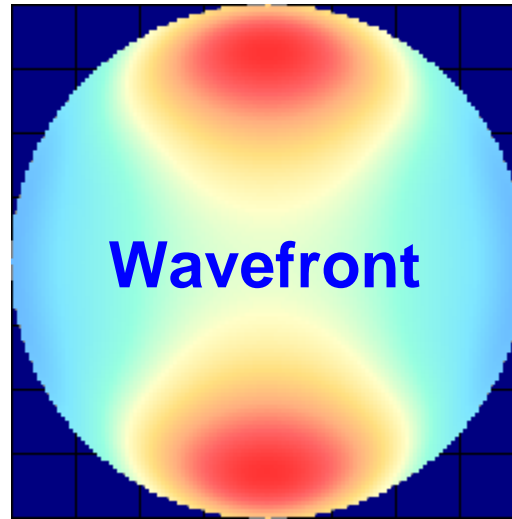
**The Nikon intelligent illuminator can support 10,000 - 100,000 DPF**

# Fast Thermal Aberration Prediction

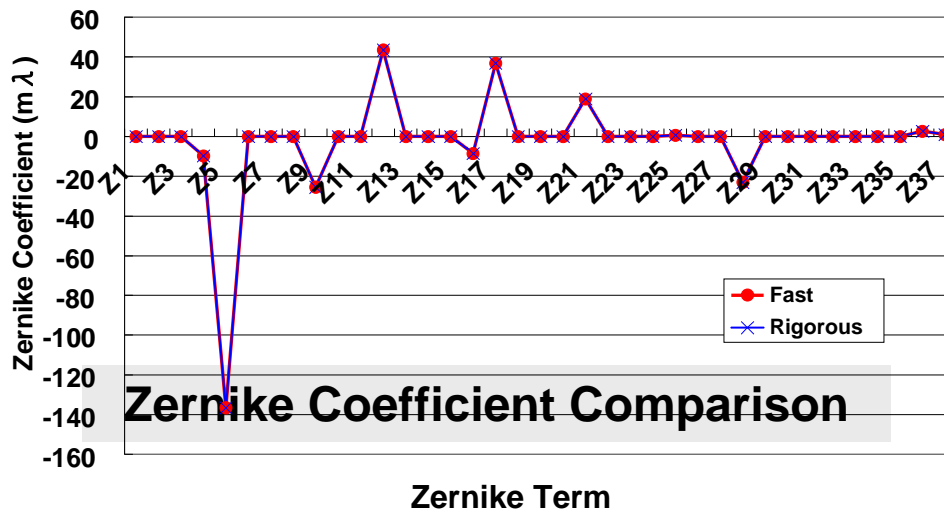
Rigorous simulation



Fast prediction



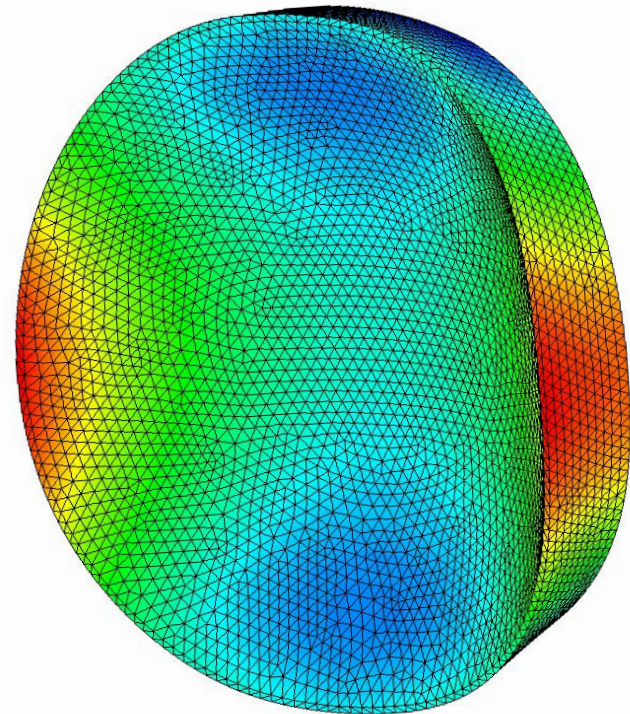
Wavefront after one hour at center of the field (0, 0)



- Accurate thermal aberration prediction available in a few seconds for any shape of diffracted pupilgram

# Thermal Aberration Control

- New adaptive optics = Deformable mirror

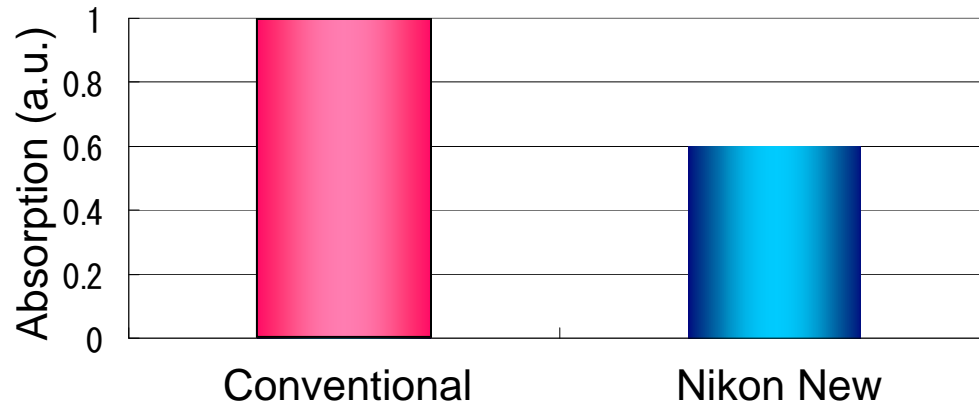


**Accurate & Quick motion**

# Lens Heating Reduction

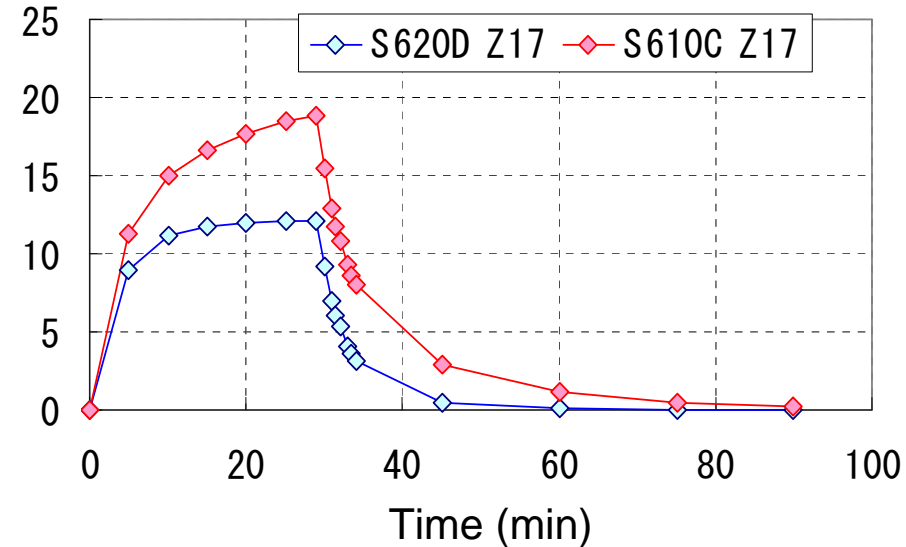
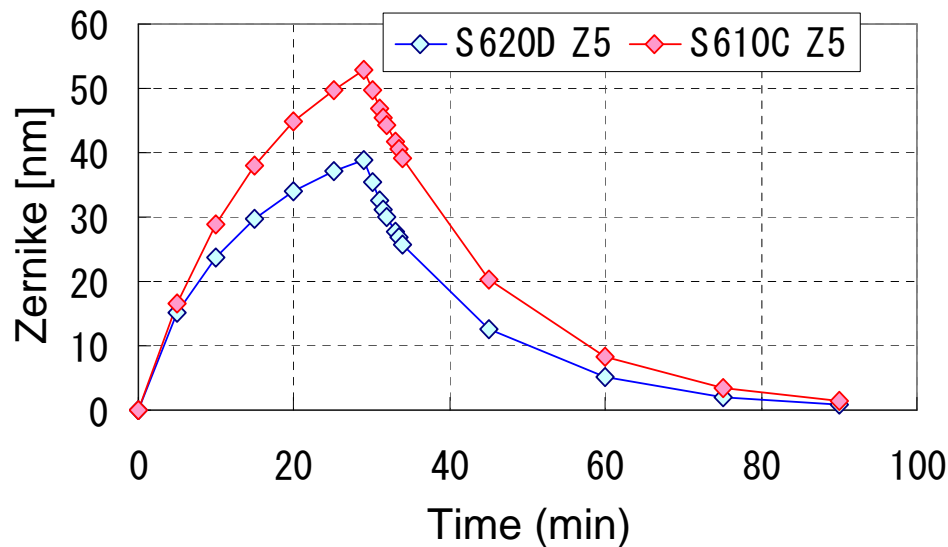


- Lens material absorption is reduced



40% reduction in absorption achieved with in-house materials development

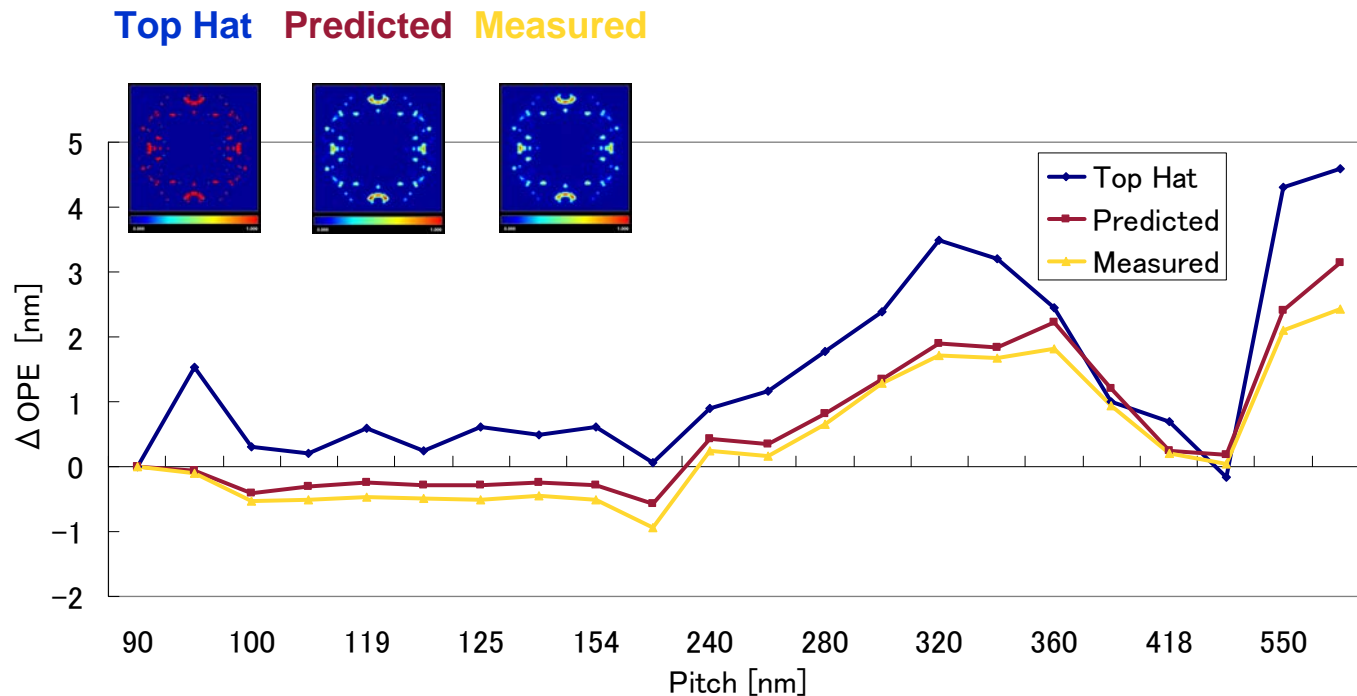
- Thermal aberration has been reduced



# OPE Matching Software



- Adjusts tool parameters (NA, iNA, A.R., etc) to minimize OPE error from reference
- Freeform-illuminator capable
- Nikon-to-Nikon and Nikon-to-Other



**Experimental result of OPE matching accuracy < 1.0 nm RMS**

# Breaking the $k_1$ Barrier



- The scanner enables computational lithography via those automatic adjustments
- We can't break the  $k_1$  barrier... but we can cheat it using extensions in the litho process
- Extensions include:
  - double patterning
  - spacer process
  - spacer and cutting
  - integration with block copolymer self-assembly

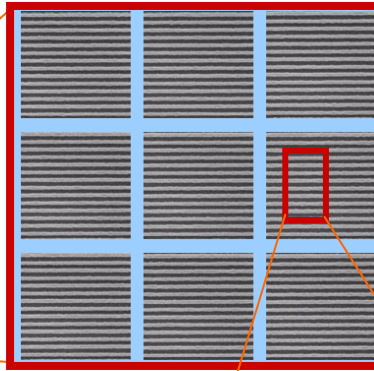
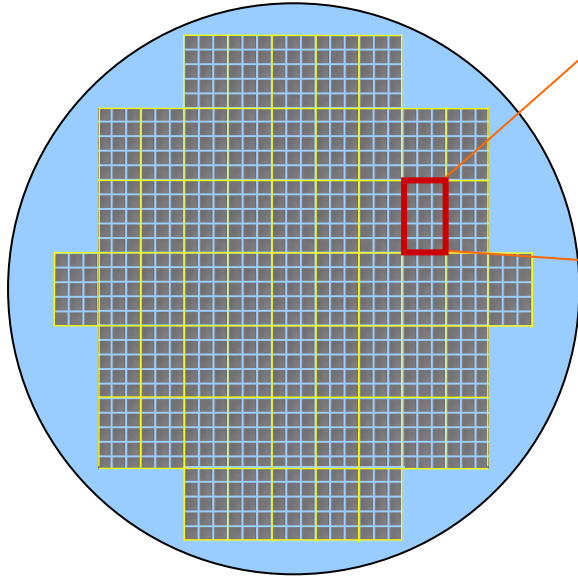


Photo: U.S. Navy

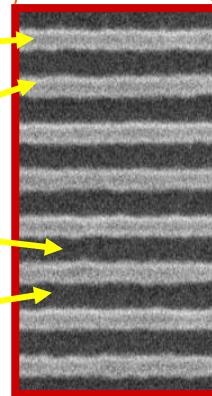


# Optical Litho: Pitch Splitting DP

LELE example (32 nm hp)

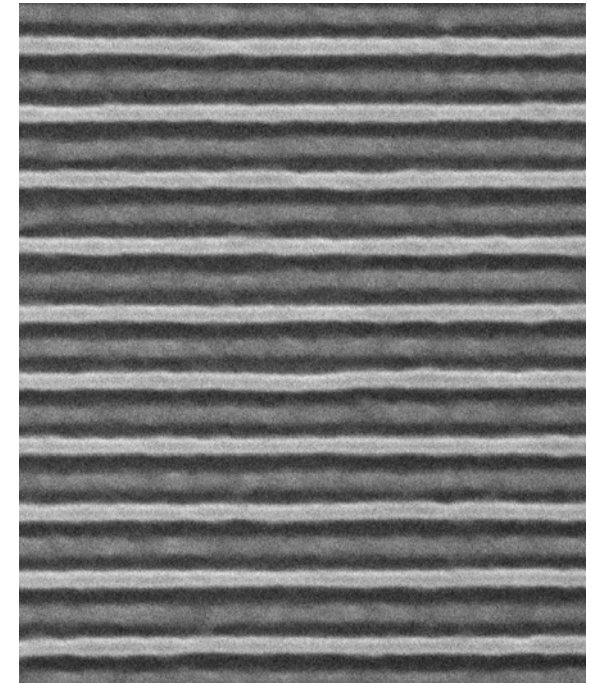


Line 1  
Line 2  
Space 1  
Space 2



|                         |        |
|-------------------------|--------|
| Line CDU ( $3\sigma$ )  | 2.5 nm |
| Space CDU ( $3\sigma$ ) | 3.3 nm |

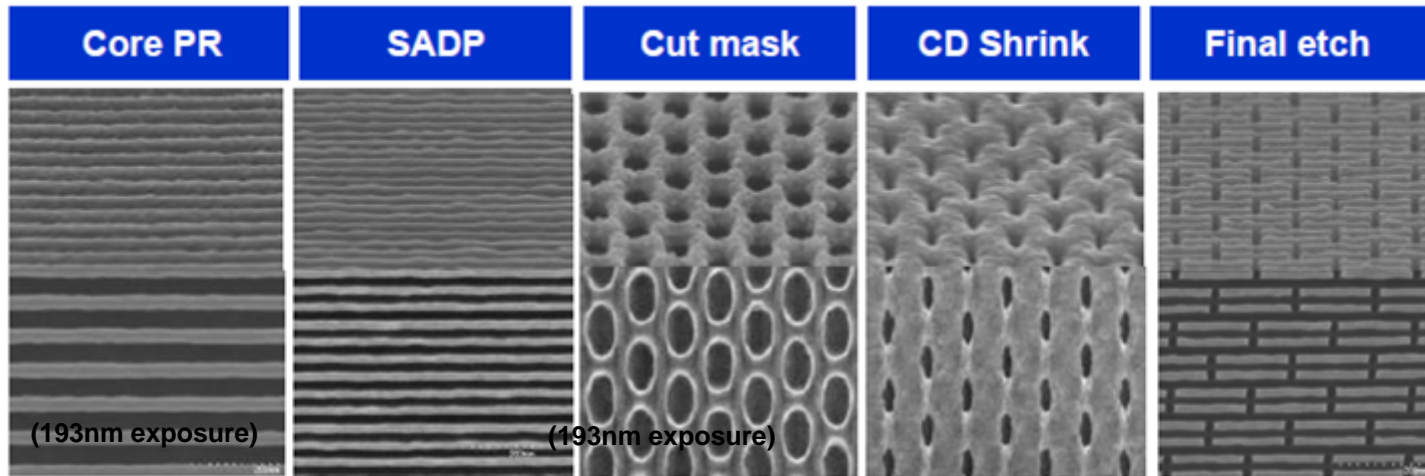
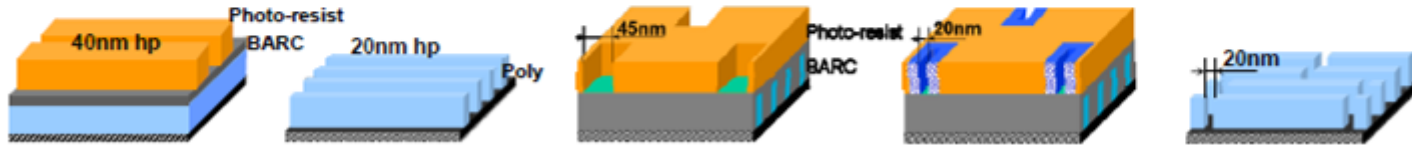
LFLE 22 nm hp



**The S620 has already supported double patterning**

# Spacer + Cutting by 193 nm Exposure

## “Spacer & Cut” Process



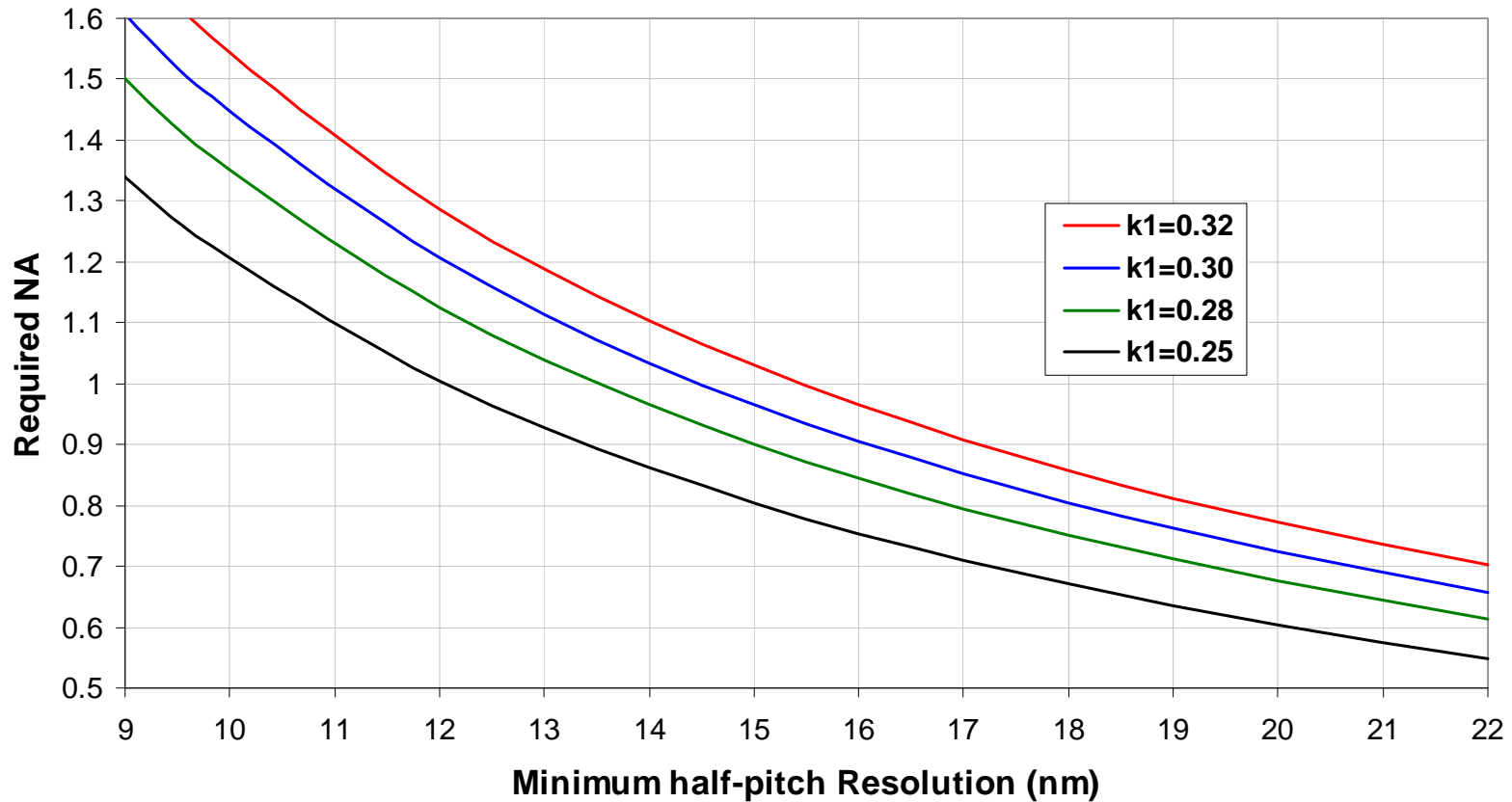


# Required NA for Double Spacer



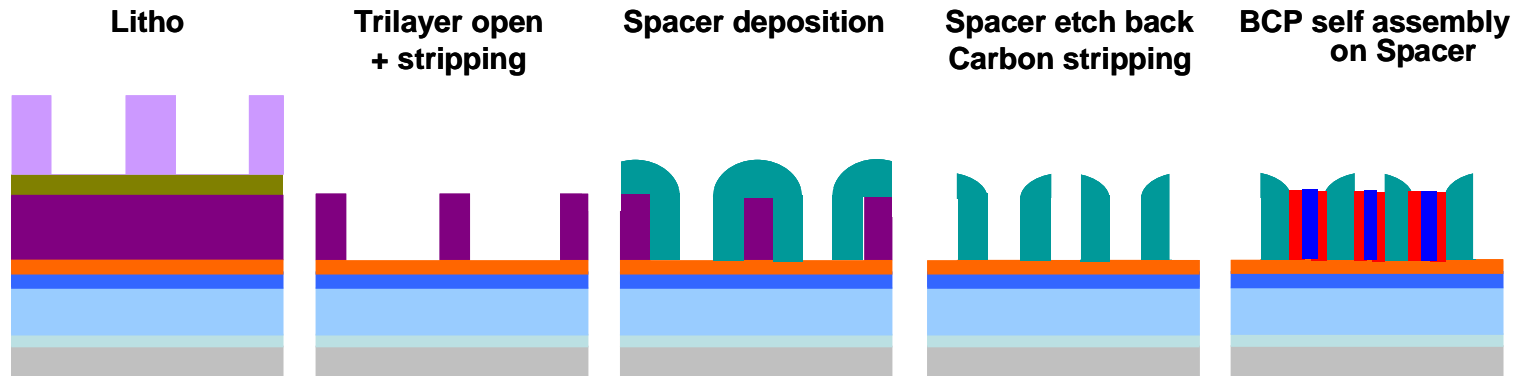
Required NA given by:  $NA = k_1 \frac{\lambda}{4d}$ ,

where  $d$  is the minimum resolution defined by deposition

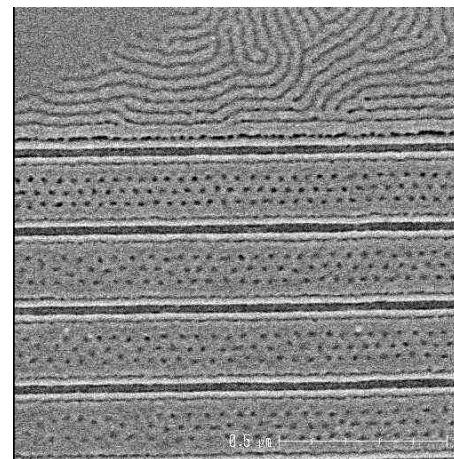
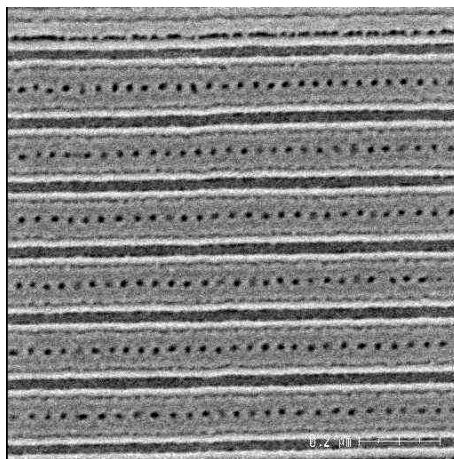


*D. Flagello, NRCA*

# Extension of 193 nm with BCP



PSbPMMA 70/30 BCP  
spacer patterns



**BCP self assembly compatible with spacer technology**

*Courtesy of R.Tiron, et al. Directed self assembly program in LETI*

- Nikon will support ArFi extension prior to EUVL
- Advanced tool control and matching will be key enablers, and the S620 has that technology in place
- Work is ongoing to combine other lithography techniques with conventional optical litho
  - Achieving 1X nm lithography with optical litho may be possible with more 'tools' added to the core techniques



**NIKON PRECISION INC.**